ON Semiconductor®

Product Bulletin

Document # : PB22229X
Issue Date: 28 March 2018

Title of Change:	Update datasheet of EFC3J018NUZ, Changing from VGSS 10V to VGSS 12V
Effective date:	28 March 2018
Contact information:	Contact your local ON Semiconductor Sales Office or <Osamu Akaki@onsemi.com>
Type of notification:	This Product Bulletin is for notification purposes only. ON Semiconductor will proceed with implementation of this change upon publication of this Product Bulletin.
Change category:	☐ Wafer Fab Change ☐ Assembly Change ☐ Test Change ☒ Other Datasheet Update

Change Sub-Category(s):

☐ Manufacturing Site Change/Addition
☐ Manufacturing Process Change
☐ Material Change
☐ Product specific change
☒ Datasheet/Product Doc change
☐ Shipping/Packaging/Marking
☐ Other: _____

Sites Affected:	ON Semiconductor Sites: None	External Foundry/Subcon Sites: None

Description and Purpose:

This Product Bulletin updates the datasheet in order to change the characteristic of VGSS suitable for the customer's application use. Updating this datasheet does not change other characteristics of the current datasheet.

Old Datasheet

SPECIFICATIONS
ABSOLUTE MAXIMUM RATINGS at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V_{SSS}	20	V
Gate to Source Voltage	V_{GSS}	±10	V
Maximum Operating Gate to Source Voltage (Note 2)	$V_{GSS(OP)}$	±8	V
Source Current (DC)	I_S	23	A
Source Current (Pulse) PW ≤ 100 μs, duty cycle ≤ 1%	I_{SP}	100	A
Total Dissipation (Note 3)	P_T	2.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note 2 : Functional operation above the stresses listed in the recommended operating ranges is not implied. Extended exposure to stresses beyond the recommended operating ranges limits may affect device reliability

New Datasheet

SPECIFICATIONS
ABSOLUTE MAXIMUM RATINGS at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V_{SSS}	20	V
Gate to Source Voltage	V_{GSS}	±12	V
Maximum Operating Gate to Source Voltage (Note 2)	$V_{GSS(OP)}$	±8	V
Source Current (DC)	I_S	23	A
Source Current (Pulse) PW ≤ 100 μs, duty cycle ≤ 1%	I_{SP}	100	A
Total Dissipation (Note 3)	P_T	2.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note 2 : Functional operation above the stresses listed in the recommended operating ranges is not implied. Extended exposure to stresses beyond the recommended operating ranges limits may affect device reliability

List of Affected Standard Parts:

EFC3J018NUZTDG

Appendix A: Changed Products

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Product	Customer Part Number
EFC3J018NUZTDG	